

N-channel 30 V 1.15 m $\Omega$  logic level MOSFET in LFPAK using NextPower technology

15 January 2015

**Product data sheet** 

#### 1. General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 2. Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, & QOSS for high system efficiencies at low and high loads
- Ultra low Rdson and low parasitic inductance

#### 3. Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching
- Power OR-ing
- Server power supplies
- Sync rectifier

#### 4. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	30	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 2</u>	[1]	-	-	100	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	272	W
Tj	junction temperature			-55	-	175	°C
Static chara	cteristics	1					
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 12		-	1.1	1.4	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 12		-	0.85	1.15	mΩ

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Dynamic chara	Dynamic characteristics						
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; Fig. 14; Fig. 15		-	14.6	26	nC
Q <sub>G(tot)</sub>	total gate charge	$V_{GS}$ = 4.5 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; Fig. 15; Fig. 14		-	50	70	nC

[1] Continuous current is limited by package.

### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G
4	G	gate	មុប្បូប្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

### 6. Ordering information

Table 3. Ordering in	formation					
Type number	Package					
	Name	Description	Version			
PSMN1R0-30YLC	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN1R0-30YLC	1C030L

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	30	V
V <sub>DGR</sub>	drain-gate voltage	25 °C $\leq$ T <sub>j</sub> $\leq$ 175 °C; R <sub>GS</sub> = 20 k $\Omega$	-	30	V
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Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>GS</sub>	gate-source voltage			-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	272	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	100	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>	[1]	-	100	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 3		-	1450	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
V <sub>ESD</sub>	electrostatic discharge voltage	MM (JEDEC JESD22-A115)		960	-	V
Source-drai	n diode	1				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	100	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	1450	А
Avalanche r	ruggedness	·				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 100 A; V <sub>sup</sub> ≤ 30 V; R <sub>GS</sub> = 50 Ω; unclamped; Fig. 4		-	259	mJ

[1] Continuous current is limited by package.

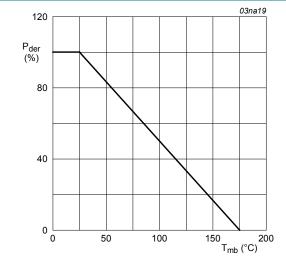
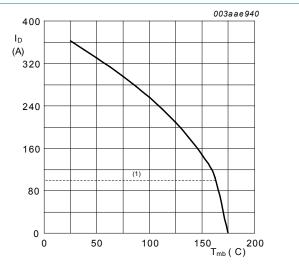
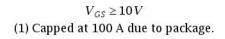


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

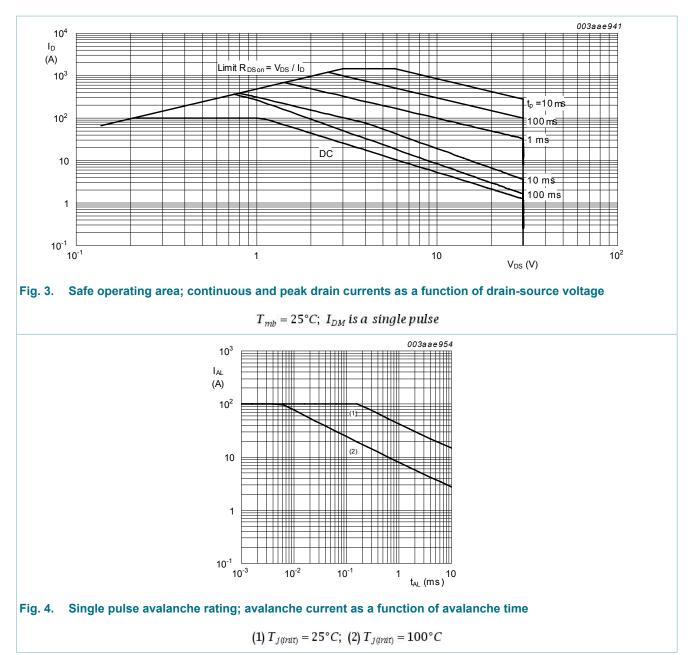
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$



## Fig. 2. Continuous drain current as a function of mounting base temperature



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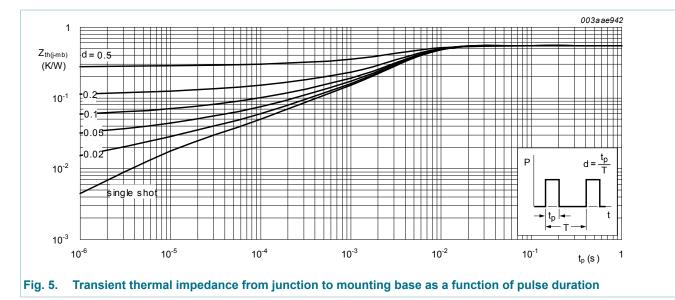
### 9. Thermal characteristics

Table 6. Th	nermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	0.45	0.55	K/W

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### **10. Characteristics**

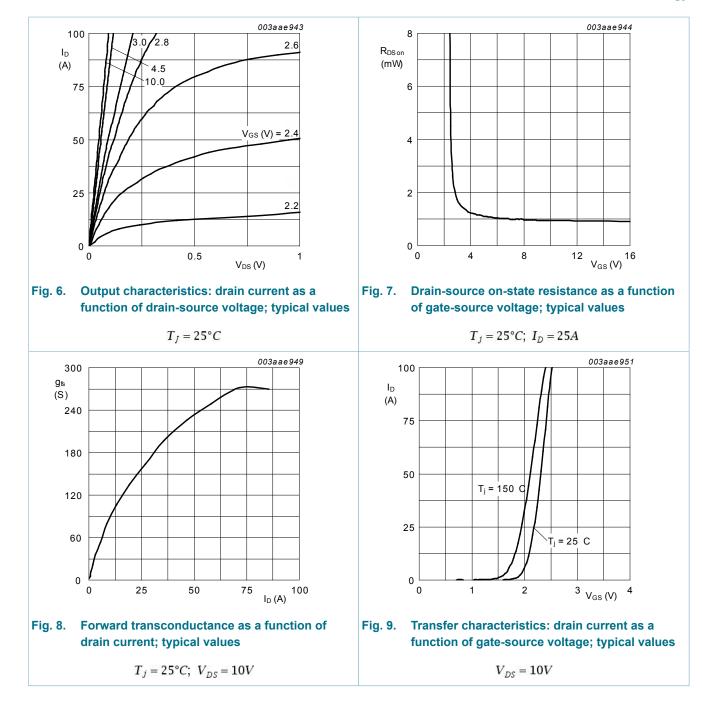
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · · ·				
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	30	-	-	V
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	27	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; Fig. 10	1.05	1.41	1.95	V
		I <sub>D</sub> = 10 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 150 °C; Fig. 11	0.5	-	-	V
	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; Fig. 11	-	-	2.25	V	
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 30 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	1	μA
		$V_{DS}$ = 30 V; $V_{GS}$ = 0 V; $T_j$ = 150 °C	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
		$V_{GS}$ = -16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 12	-	1.1	1.4	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 150 °C; Fig. 12; Fig. 13	-	-	2.4	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>	-	0.85	1.15	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 150 °C; Fig. 12; Fig. 13	-	-	1.85	mΩ

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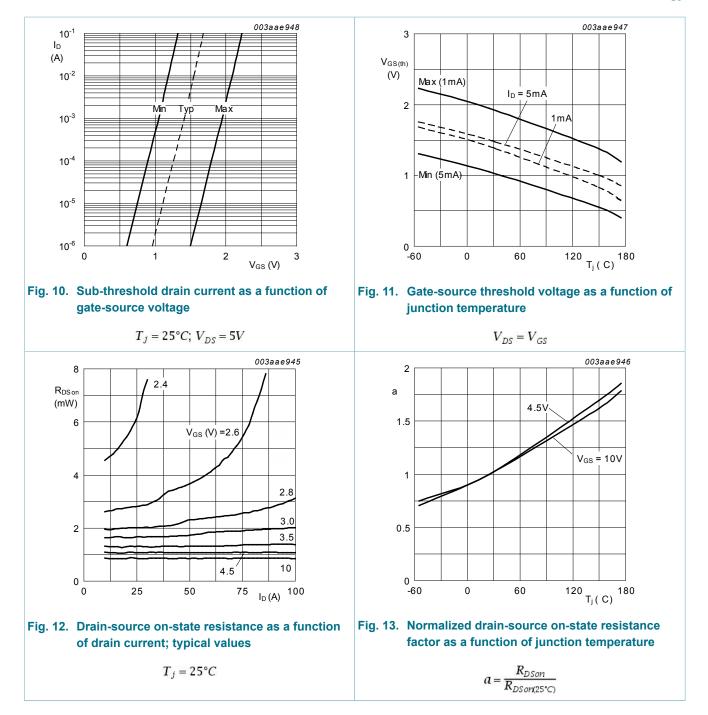
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>G</sub>	gate resistance	f = 1 MHz	-	1.1	2.2	Ω
Dynamic cł	naracteristics	· · ·		1		
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15	-	103.5	145	nC
		I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 4.5 V; Fig. 15; Fig. 14	-	50	70	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}; \frac{\text{Fig. 15}}{10000000000000000000000000000000000$	-	96.5	-	nC
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 4.5 V;	-	12.9	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	Fig. 14; Fig. 15	-	10.1	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	2.8	-	nC
Q <sub>GD</sub>	gate-drain charge		-	14.6	26	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; <u>Fig. 14</u>	-	2.2	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	3322	6645	9968	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	605	1210	1815	pF
C <sub>rss</sub>	reverse transfer capacitance		240	481	842	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 15 V; R <sub>L</sub> = 0.6 Ω; V <sub>GS</sub> = 4.5 V;	-	44	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	77	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	108	-	ns
t <sub>f</sub>	fall time		-	60	-	ns
Q <sub>oss</sub>	output charge	$V_{GS}$ = 0 V; $V_{DS}$ = 15 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	35.2	-	nC
Source-dra	in diode	· · ·		1		
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 25 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; Fig. 17	-	0.8	1.1	V
t <sub>rr</sub>	reverse recovery time	$I_{\rm S}$ = 25 A; dI_{\rm S}/dt = -100 A/µs; V <sub>GS</sub> = 0 V;	-	45	-	ns
Qr	recovered charge	V <sub>DS</sub> = 15 V	-	67	-	nC
t <sub>a</sub>	reverse recovery rise time	$I_{S}$ = 25 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 15 V; Fig. 18	-	28.5	-	ns
t <sub>b</sub>	reverse recovery fall time		-	16.5	-	ns

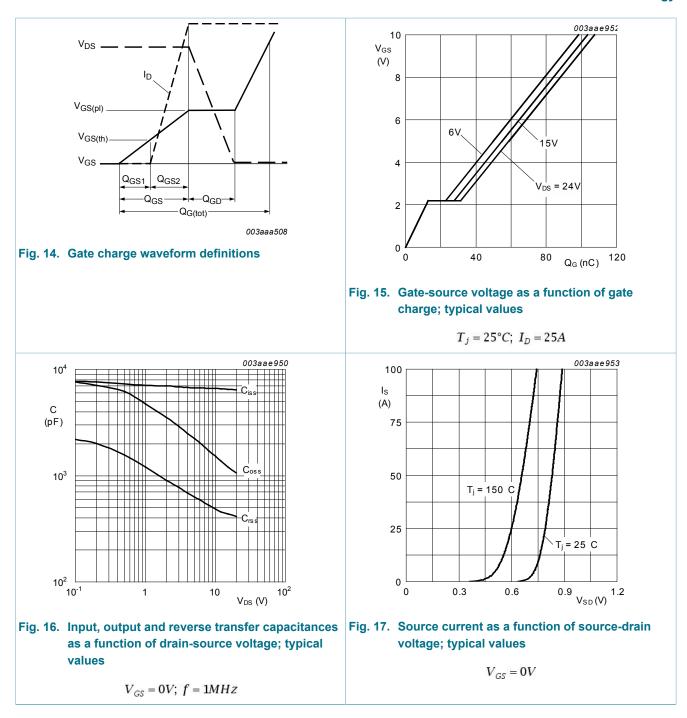
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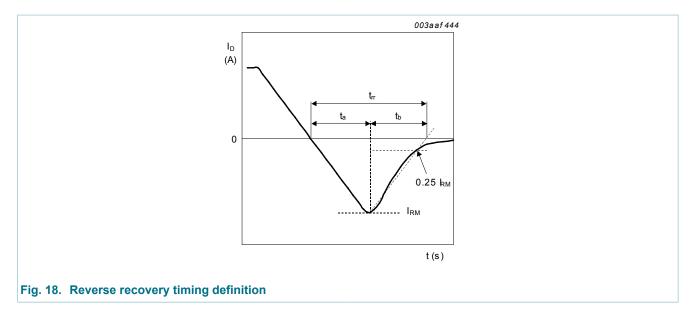


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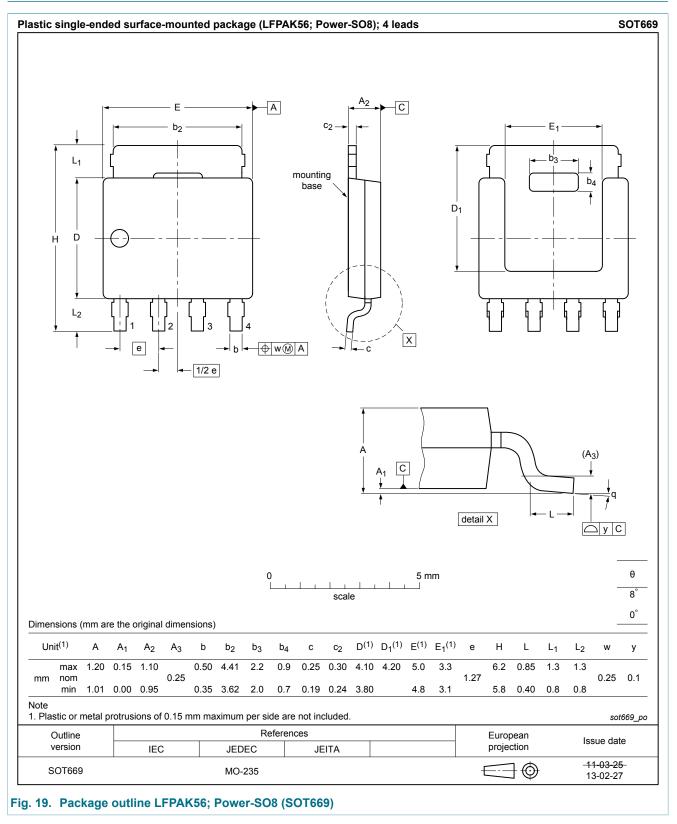
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### **11. Package outline**



PSMN1R0-30YLC

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